



Micro Commercial Components  
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# BAV19W THRU BAV21W

## Features

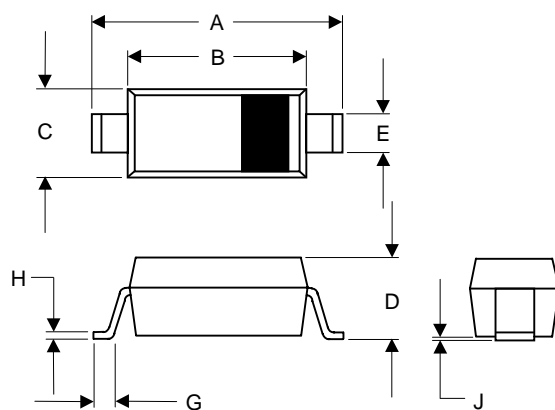
- Silicon Epitaxial Planar Diodes
- For General Purpose
- This diode is also available in other case.

**410mW**  
**Small Signal**  
**Diodes**  
**120 to 250 Volts**

## Mechanical Data

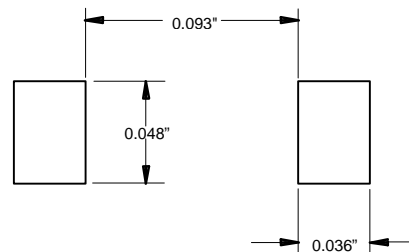
- Case: SOD-123, Molded Plastic
- Weight: approx. 0.01g
- Marking code: BAV19W=A8  
 BAV20W=T2  
 BAV21W=T3

## SOD123



DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	.140	.152	3.55	3.85	
B	.100	.112	2.55	2.85	
C	.055	.071	1.40	1.80	
D	-----	.053	-----	1.35	
E	.012	.031	0.30	.78	
G	.006	-----	0.15	-----	
H	-----	.01	-----	.25	
J	-----	.006	-----	.15	

### SUGGESTED SOLDER PAD LAYOUT



## Maximum Ratings

Symbol	Rating	Rating	Unit
$V_R$	Continuous Reverse Voltage	BAV19W 100 BAV20W 150 BAV21W 200	V
$V_{RRM}$	Repetitive Peak Reverse Voltage	BAV19W 120 BAV20W 200 BAV21W 250	V
$I_F$	Forward DC Current at $T_{amb}=25^{\circ}C^{(1)}$	250	mA
$I_{F(AV)}$	Rectified Current (Average) Half Wave Rectification with Resist. Load at $T_{amb}=25^{\circ}C^{(1)}$	200	mA
$I_{FRM}$	Repetitive Peak Forward Current at $f>50Hz$ , $T_{amb}=25^{\circ}C^{(1)}$	625	mA
$I_{FSM}$	Surge Forward Current at $t<1s$ , $T_j=25^{\circ}C$	1.0	A
$P_{Tot}$	Power Dissipation at $T_{amb}=25^{\circ}C^{(1)}$	410	mW
$R_{JA}$	Thermal Resistance Junction to Ambient Air	375	mW
$T_j$	Junction Temperature	-55 to +150	$^{\circ}C$
$T_{STG}$	Storage Temperature	-55 to +150	$^{\circ}C$

## Electrical Characteristics @ 25°C Unless Otherwise Specified

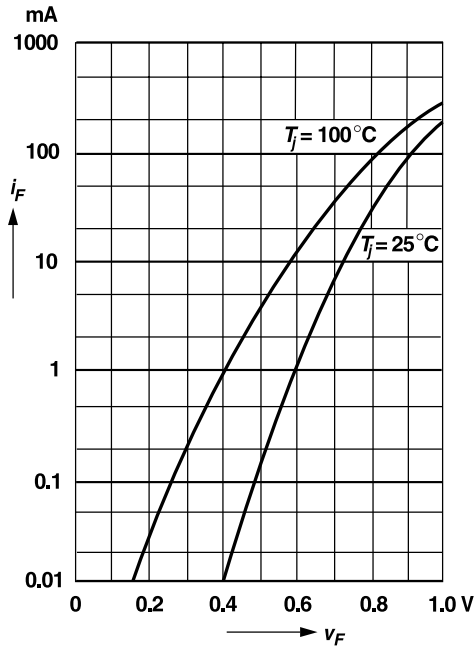
Symbol	Parameter	Min	Typ	Max	Units
$V_F$	Forward Voltage ( $I_F=100mA$ ) ( $I_F=200mA$ )	---	---	1.00 1.25	V
$I_R$	Leakage Current ( $V_R=100V$ ) ( $V_R=100V, T_j=100^{\circ}C$ ) ( $V_R=150V$ ) ( $V_R=150V, T_j=100^{\circ}C$ ) ( $V_R=200V$ ) ( $V_R=200V, T_j=100^{\circ}C$ )	---	---	100 15 100 15 100 15	nA uA nA uA nA uA
$r_f$	Dynamic Forward Resistance ( $I_F=10mA$ )	---	5.0	---	OHM
$C_{tot}$	Capacitance ( $V_R=0, f=1.0MHz$ )	---	1.5	---	pF
$t_{rr}$	Reverse Recovery Time ( $I_F=30mA, I_R=30mA$ ) ( $I_{rr}=3.0mA, R_f=100OHMS$ )	---	---	50	ns

\*(1) Valid provided that leads are kept at ambient temperature

# BAV19W thru BAV21W

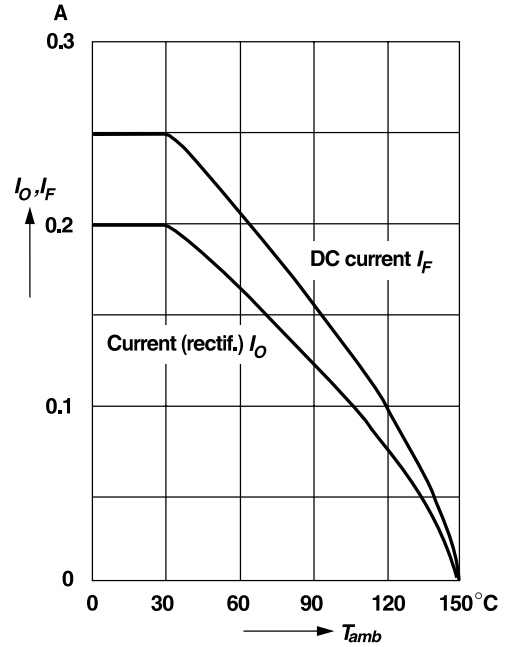


**Forward characteristics**



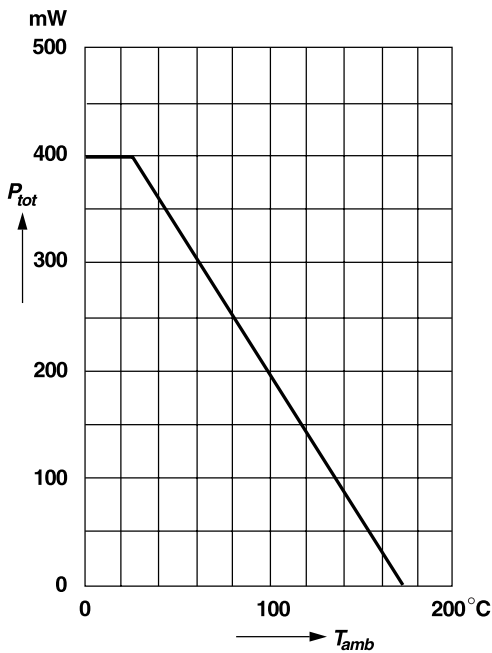
**Admissible forward current versus ambient temperature**

Valid provided that electrodes are kept at ambient temperature

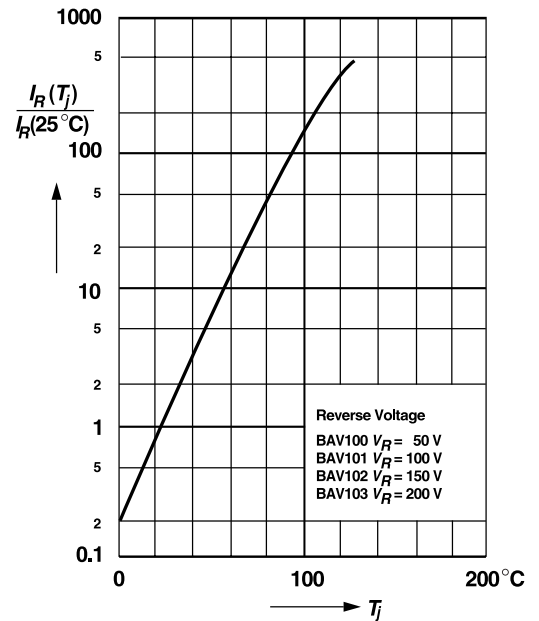


**Admissible power dissipation versus ambient temperature**

Valid provided that electrodes are kept at ambient temperature



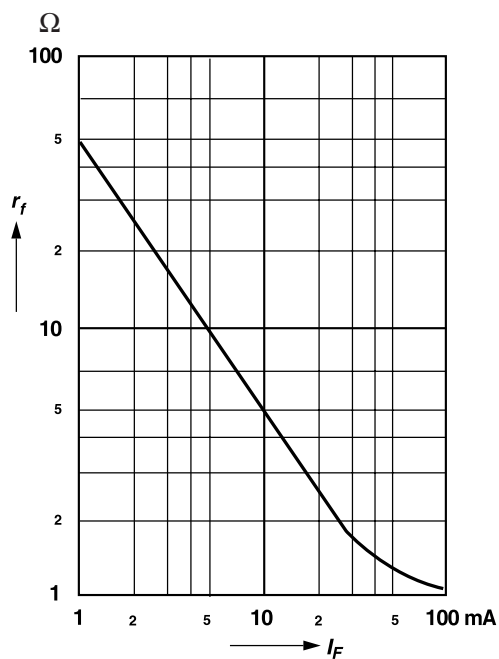
**Leakage current versus junction temperature**



# BAV19W thru BAV21W



Dynamic forward resistance versus forward current



Capacitance versus reverse voltage

